

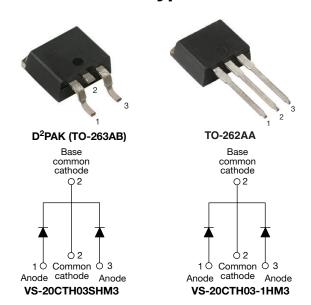
www.vishay.com

Vishay Semiconductors

HALOGEN

FREE

Hyperfast Rectifier, 2 x 10 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
I _{F(AV)}	2 x 10 A						
V_{R}	300 V						
V _F at I _F	0.85 V						
t _{rr} typ.	23 ns						
T _J max.	175 °C						
Package	D ² PAK (TO-263AB), TO-262AA						
Circuit configuration	Common cathode						

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201, class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage	V_{RRM}		300	V					
Average rectified forward current per diode	I _{F(AV)}	T _C = 160 °C	10						
per device			20	Α					
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	120						
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-	V			
Forward voltage	V _F	I _F = 10 A	-	1.05	1.25	V			
		I _F = 10 A, T _J = 125 °C	-	0.85	0.95				
Daviera la alcana accimient	1	$V_R = V_R$ rated	-	-	20				
Reverse leakage current	I _R	T _J = 125 °C, V _R = V _R rated	-	6	200	μΑ			
Junction capacitance	C _T	V _R = 300 V	-	30	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH			

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VS-20CTH03SHM3, VS-20CTH03-1HM3

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS		
		$I_F = 1.0 A, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		23	-			
Reverse recovery time	t _{rr}	$T_J = 25 ^{\circ}C$	I _F = 10 A dI _F /dt = 200 A/μs V _B = 200 V	-	31	-	ns		
		T _J = 125 °C		-	42	-			
Dook roopyony gurrant		T _J = 25 °C		-	2.4	-	Α		
Peak recovery current	IRRM	T _J = 125 °C		-	5.6	-	_ ^		
Reverse recovery charge	0	T _J = 25 °C	VH - 200 V	-	36	-	nC		
	Q _{rr}	T _J = 125 °C		-	120	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W			
Thermal resistance, junction to ambient	R _{thJA}		-	-	70	°C/W			
Weight				2.0	=.	g			
vveigni			-	0.07	-	OZ.			
Marking device		Case style D ² PAK (TO-263AB)	le D ² PAK (TO-263AB) 20CTH03SH		H03SH				
ivial Killy device	Case style TO-262AA		20CTH03-1H						

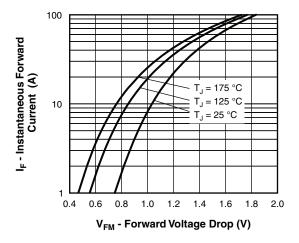


Fig. 1 - Maximum Forward Voltage Drop Characteristics

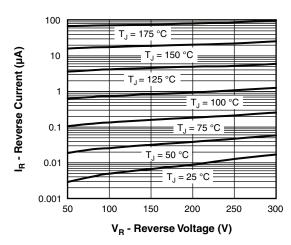


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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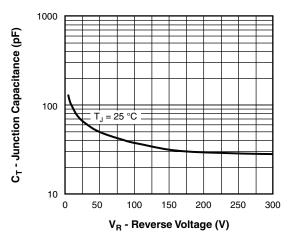


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

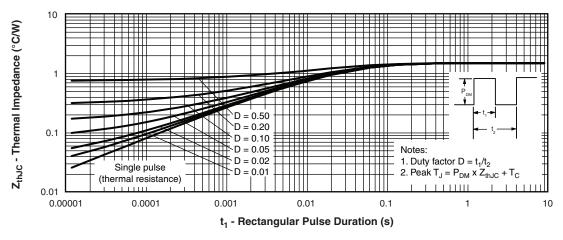


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

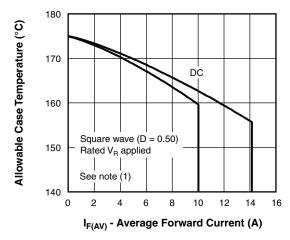


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

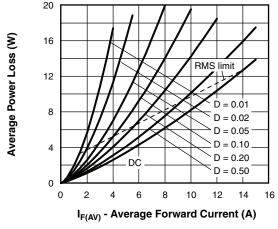


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{th,JC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

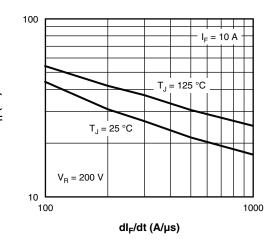


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

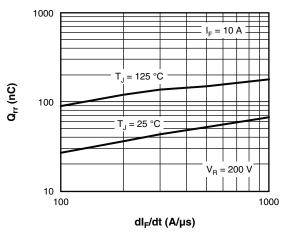
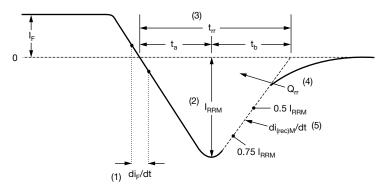


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{F}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

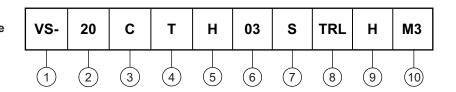
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-20CTH03SHM3, VS-20CTH03-1HM3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 A)

C = common cathode

- T = TO-220, D²PAK

H = hyperfast rectifier

Voltage rating (03 = 300 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

10 - M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

LINKS TO RELATED DOCUMENTS								
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046						
Differisions	TO-262AA	www.vishay.com/doc?95419						
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444						
Fart marking information	TO-262AA	www.vishay.com/doc?95443						
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032						
SPICE model		www.vishay.com/doc?96583						



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		ERS INCHES		NOTES	NOTES SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	ES STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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TO-262

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	NOTES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.10	D BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.36	3.71	0.132	0.146	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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